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a layer of a second conductive material disposed over the first line, the second conductive material being different from the first conductive material;
a layer of chalcogenide material disposed over the layer of the second conductive material; and
a second line formed over the layer of chalcogenide material.

16 17. (Once Amended) The memory cell, as set forth in claim 15, wherein the first line is embedded in the substrate.

B² 17 18. (Once Amended) The memory cell, as set forth in claim 15, wherein the first line is disposed in a window formed in a dielectric layer disposed over the substrate.

18 19. (Once Amended) The memory cell, as set forth in claim 15, wherein the layer of silver is deposited on the first line using an immersion plating technique.

19 20. (Once Amended) The memory cell, as set forth in claim 15, wherein the chalcogenide material comprises germanium selenide.

20 21. (Once Amended) A memory cell comprising:

a first layer of dielectric material disposed over a substrate, the first layer of dielectric material having a first window therein;

a first line disposed in the first window, the first line being formed of a first conductive material that comprises one of aluminum, copper, nickel, and tungsten;

β^2

a second layer of dielectric material disposed over the first layer of dielectric material and over the first line, the second layer of dielectric material having a second window therein, the second window exposing at least a portion of the first line;

a layer of a second conductive material disposed in the second window over the first line, the second conductive material being different from the first conductive material;

a layer of chalcogenide material disposed in the second window over the layer of the second conductive material; and

a second line formed over the layer of chalcogenide material.

β^3 24 26. (Once Amended) A memory cell comprising:

a first layer of dielectric material disposed over a substrate, the first layer of dielectric material having a first window therein;

a first line disposed in the first window, the first line being formed of a first conductive material that comprises one of aluminum, copper, nickel, and tungsten;

a second layer of dielectric material disposed over the first layer of dielectric material and over the first line;

a first layer of conductive material disposed over the second layer of dielectric material, the first layer of conductive material and the second layer of dielectric material having a second window therein, the second window exposing at least a portion of the first line;

a layer of a second conductive material disposed in the second window over the first line, the second conductive material being different from the first conductive material;

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a layer of chalcogenide material disposed in the second window over the layer of the
second conductive material; and
a second line formed over the layer of chalcogenide material and over the first layer of
conductive material.

28 31. (Once Amended) A memory comprising:

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a memory array having a plurality of memory cells, each of the memory cells comprising:
a first line formed over a substrate, the first line being formed of a first conductive
material that comprises one of aluminum, copper, nickel, and tungsten;
a layer of a second conductive material disposed over the first line, the second conductive
material being different from the first conductive material;
a layer of chalcogenide disposed over the layer of the second conductive material; and
a second line formed over the layer of chalcogenide.

34 38. (Once Amended) An electronic device comprising:

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a processor;
a memory operatively coupled to the processor, the memory comprising a memory array
having a plurality of memory cells, each of the memory cells comprising:
a first line formed over a substrate, the first line being formed of a first conductive
material that comprises one of aluminum, copper, nickel, and tungsten;
a layer of a second conductive material disposed over the first line, the second conductive
material being different from the first conductive material;